

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1.-13. Canceled:

14. (Currently Amended) A nitride semiconductor device comprising:

an active layer of a quantum well structure which has a first surface and a second surface and which comprises an indium-containing nitride semiconductor;

a first layer which adjoins the first surface of the active layer and has a band gap energy larger than that of the active layer;

a second layer which is a light guiding layer and is formed on the first surface side of the active layer at a location more distant from the active layer relative to the first layer and which comprises a nitride semiconductor containing an acceptor impurity and which has a band gap energy smaller than that of the first layer; and

a third layer which is formed on the first surface side of the active layer at a location more distant from the active layer relative to the second layer and which comprises a nitride semiconductor containing an acceptor impurity and which has a band gap energy larger than that of the second layer.

15. (Original) the device according to claim 14, wherein said first layer has a thickness sufficiently thin such that carriers may tunnel therethrough.

16. (Original) The device according to claim 14, wherein said first layer has a thickness of 0.1  $\mu\text{m}$  or less.

17. (Original) The device according to claim 16, wherein said first layer has a thickness of 10 angstroms or more.

18. (Original) The device according to claim 14, wherein said active layer is doped with an impurity.

19. (Original) The device according to claim 18, wherein said impurity comprises silicon or germanium

20. (Currently Amended) The device according to claim 18, wherein said impurity is doped in ~~said~~ at least one well layer in said active layer.

21. (Original) The device according to claim 14, wherein said second layer adjoins said first layer.

22. (Original) The device according to claim 21, wherein said third layer adjoins said second layer.

23.-52. Canceled.

48.-53. Canceled.